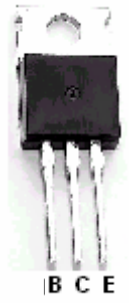
Silicon PNP Power Transistors 2SA1289

DESCRIPTION

- With TO-220 package
- Complement to type 2SC3253
- Low saturation voltage
- Short switching time

APPLICATIONS

- Various inductance lamp drivers for electrical equipment
- Inverters;converters
- Power amplification
- Switching regulator ,driver



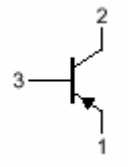


Fig.1 simplified outline (TO-220) and symbol

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-80	V
V_{CEO}	Collector-emitter voltage	Open base	-60	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-5	A
I_{CM}	Collector current-Peak		-7	A
P_C	Collector power dissipation	T_C=25℃	30	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

Silicon PNP Power Transistors 2SA1289

CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-1mA ,R_{BE}=∞	-60			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=-1mA; I_E=0	-80			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=-1mA; I_C=0	-5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-2.5A; I_B=-0.125A			-0.4	V
I_{CBO}	Collector cut-off current	V_{CB}=-40V; I_E=0			-100	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-4V; I_C=0			-100	μA
h_{FE}	DC current gain	I_C=-1A ; V_{CE}=-2V	70		280	
f_T	Transition frequency	I_C=-1A ; V_{CE}=-5V		100		MHz

◆ **h_{FE} Classifications**

Q	R	S
70-140	100-200	140-280

Silicon PNP Power Transistors 2SA1289

PACKAGE OUTLINE

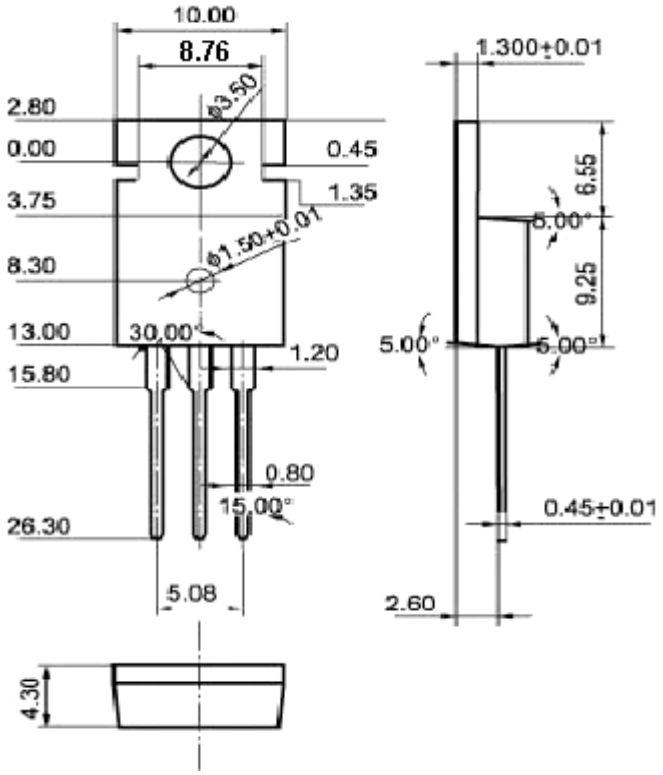


Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)

Silicon PNP Power Transistors 2SA1289

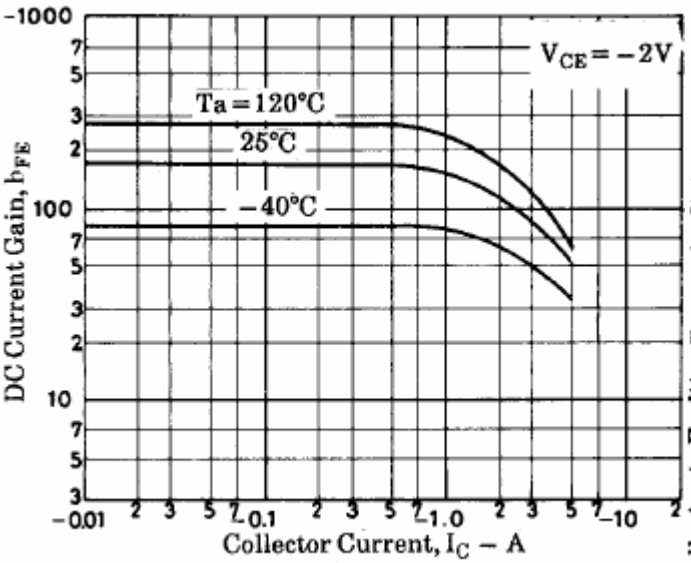


Fig.3 DC current Gain

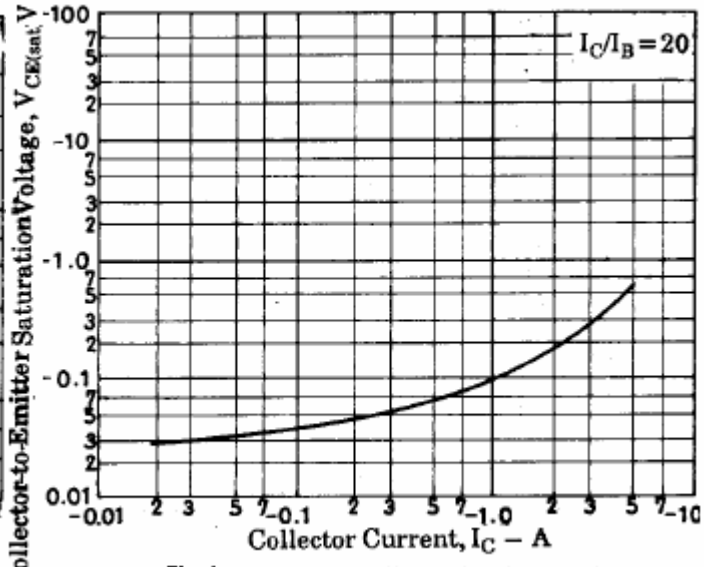


Fig.4 Collector-Emitter Saturation Voltage

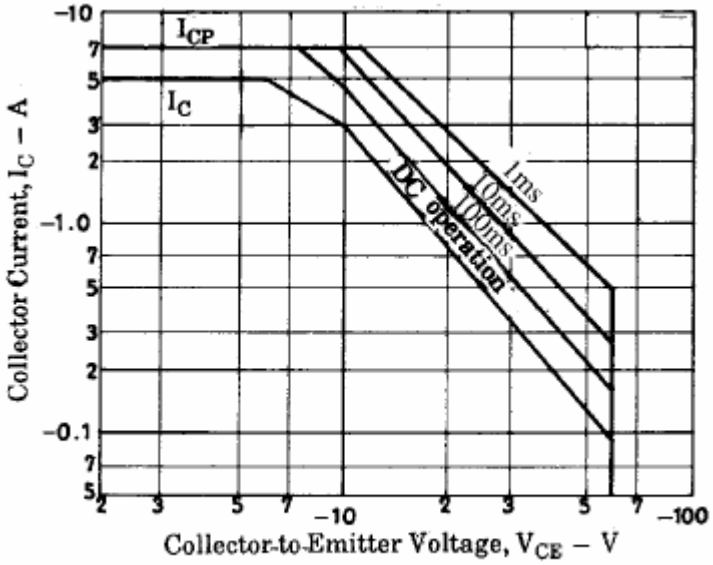


Fig.5 Safe Operating Area